



Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

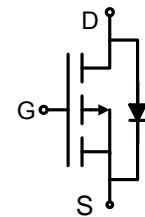
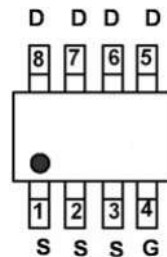
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

| | | |
|-------------------------------|-----|----|
| BVDSS | -20 | V |
| $R_{DS(on), Typ@V_{GS}=-10V}$ | 6.0 | mΩ |
| I_D | -13 | A |



SOP-8



Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

| Parameter | Symbol | Rating | Unit |
|--------------------------------------|-----------------------------|------------|------------------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current | $I_D@T_C=25^\circ\text{C}$ | -13 | A |
| | $I_D@T_C=75^\circ\text{C}$ | -8.36 | A |
| | $I_D@T_C=100^\circ\text{C}$ | -6.93 | A |
| Pulsed Drain Current ^① | I_{DM} | -52 | A |
| Total Power Dissipation ^② | $P_D@T_C=25^\circ\text{C}$ | 3.6 | W |
| Total Power Dissipation | $P_D@T_A=25^\circ\text{C}$ | 0.69 | W |
| Operating Junction Temperature | T_J | -55 to 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{STG} | -55 to 150 | $^\circ\text{C}$ |
| Single Pulse Avalanche Energy | E_{AS} | 80 | mJ |

Thermal resistance

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--|------------|------|------|------|--------------------|
| Thermal resistance, junction - case ^② | R_{thJC} | - | - | 24 | $^\circ\text{C/W}$ |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 85 | $^\circ\text{C/W}$ |

**Electronic Characteristics**

| Parameter | Symbol | Condition | Min. | Typ | Max. | Unit |
|-----------------------------------|--------------|------------------------------------|------|------|-----------|------------|
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = -250\mu A$ | -20 | | | V |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = -250\mu A$ | -0.3 | -0.6 | -1.0 | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS} = -20V, V_{GS} = 0V$ | | | -1.0 | μA |
| Gate- Source Leakage Current | I_{GSS} | $V_{GS} = \pm 12V, V_{DS} = 0V$ | | | ± 100 | nA |
| Static Drain-source On Resistance | $R_{DS(ON)}$ | $V_{GS} = -10V, I_D = -8A$ | | 6.0 | 13 | m Ω |
| | | $V_{GS} = -4.5V, I_D = -6A$ | | 7.7 | 16 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS} = -10V, I_D = -5A$ | | 9 | | s |
| Source-drain voltage | V_{SD} | $I_S = -9A$ | | | 1.28 | V |

Electronic Characteristics

| Parameter | Symbol | Condition | Min. | Typ | Max. | Unit |
|------------------------------|-----------|-----------|------|------|------|------|
| Input capacitance | C_{iss} | f = 1MHz | - | 2160 | - | pF |
| Output capacitance | C_{oss} | | - | 432 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 288 | - | |

Gate Charge characteristics($T_a = 25^\circ C$)

| Parameter | Symbol | Condition | Min. | Typ | Max. | Unit |
|----------------------|----------|----------------|------|-----|------|------|
| Total gate charge | Q_g | $V_{DD} = 25V$ | - | 15 | - | nC |
| Gate - Source charge | Q_{gs} | $I_D = 8A$ | - | 4 | - | |
| Gate - Drain charge | Q_{gd} | $V_{GS} = 10V$ | - | 6 | - | |

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;



Fig.1 Power Dissipation Derating Curve

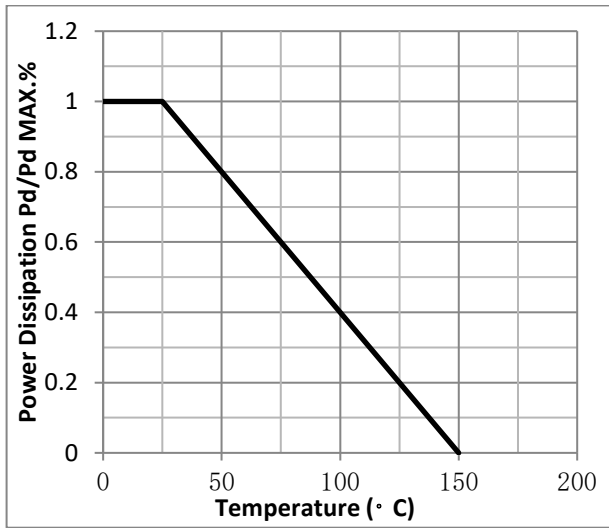


Fig.2 Typical output Characteristics

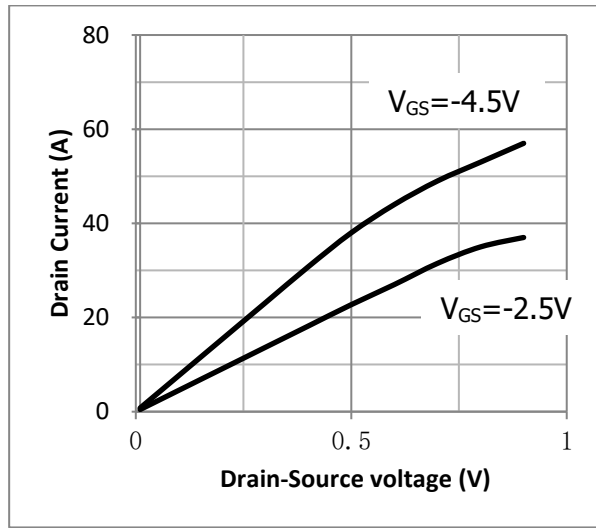


Fig.3 Threshold Voltage V.S Junction Temperature

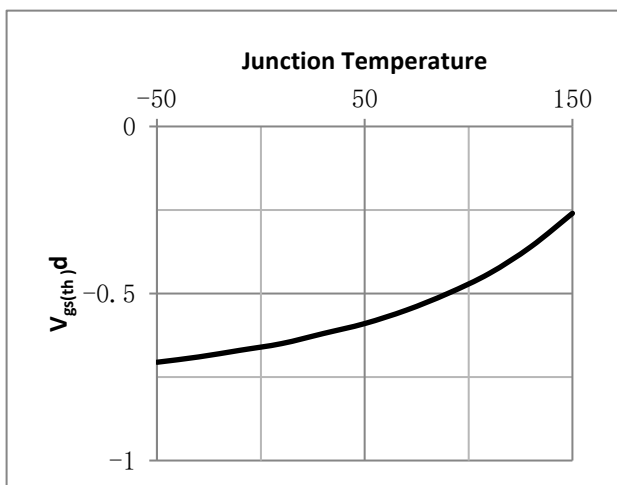


Fig.4 Resistance V.S Drain Current

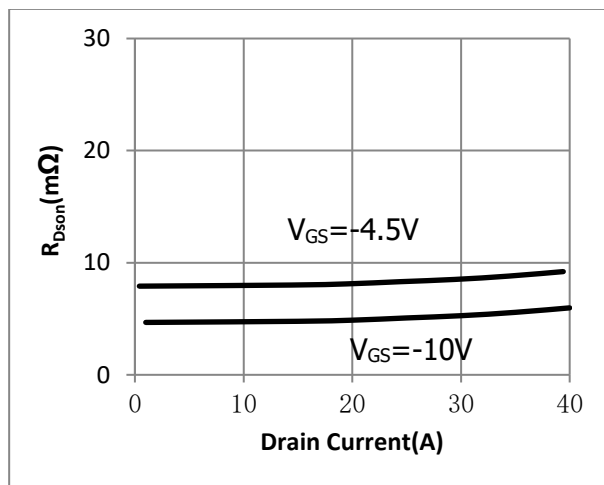


Fig.5 On-Resistance VS Gate Source Voltage

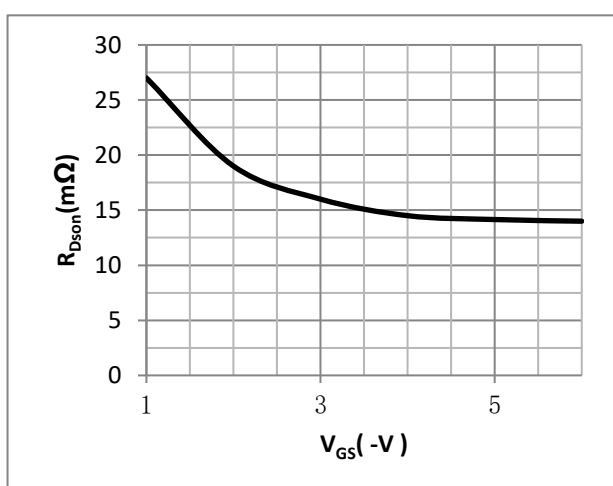


Fig.6 On-Resistance V.S Junction Temperature

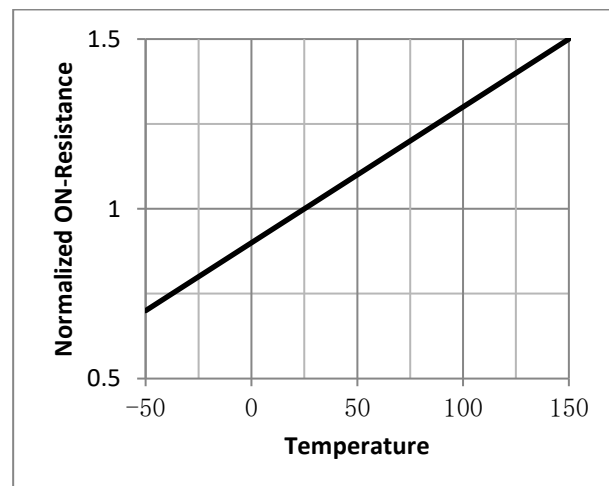


Fig.7 Switching Time Measurement Circuit

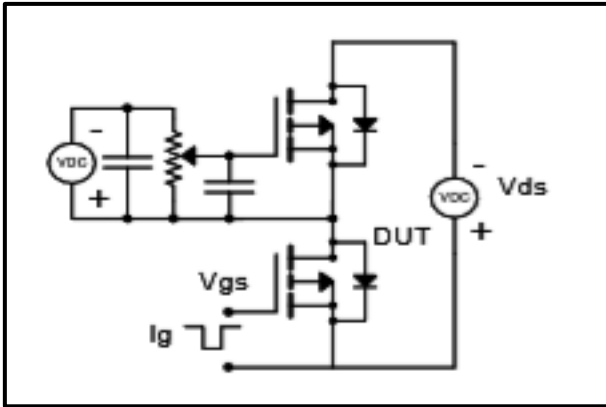


Fig.8 Gate Charge Waveform

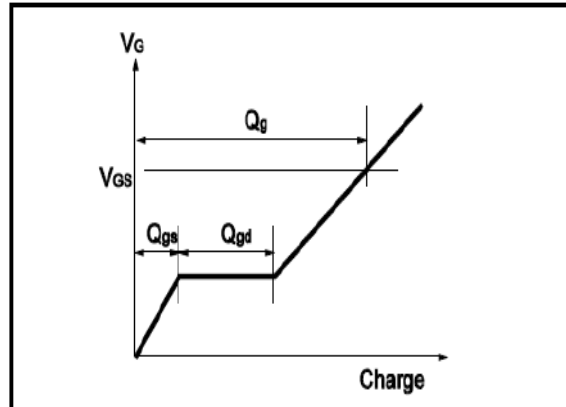


Fig.9 Switching Time Measurement Circuit

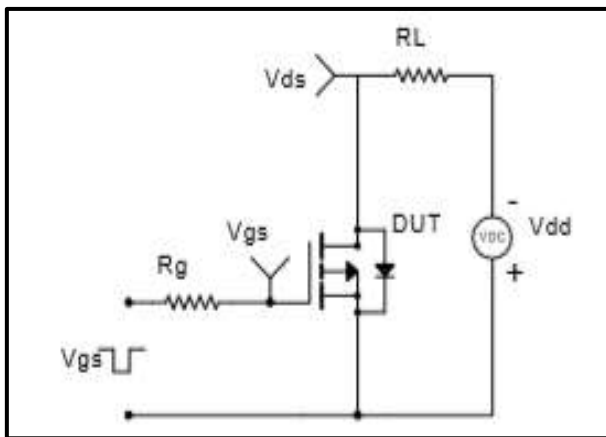


Fig.10 Gate Charge Waveform

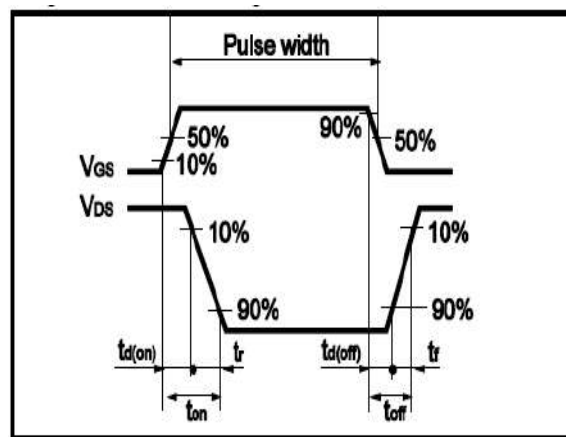


Fig.11 Avalanche Measurement Circuit

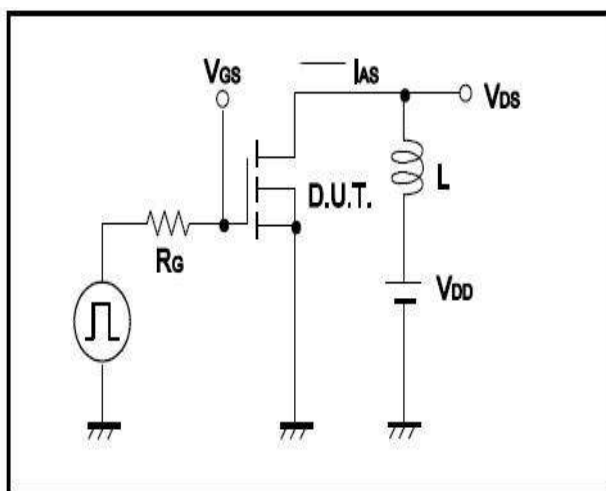
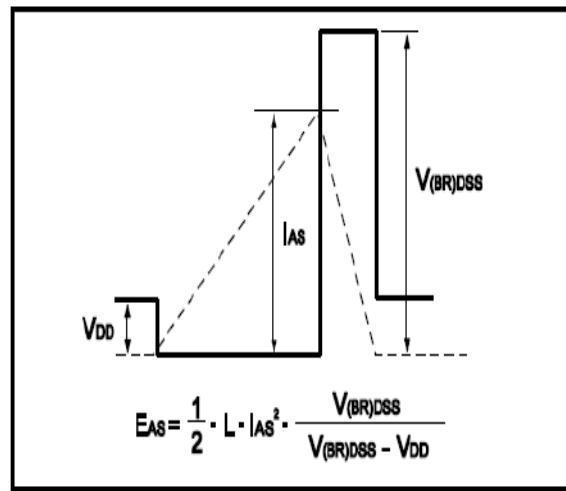
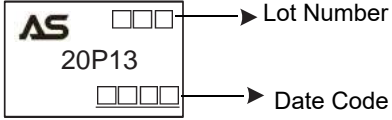


Fig.12 Avalanche Waveform

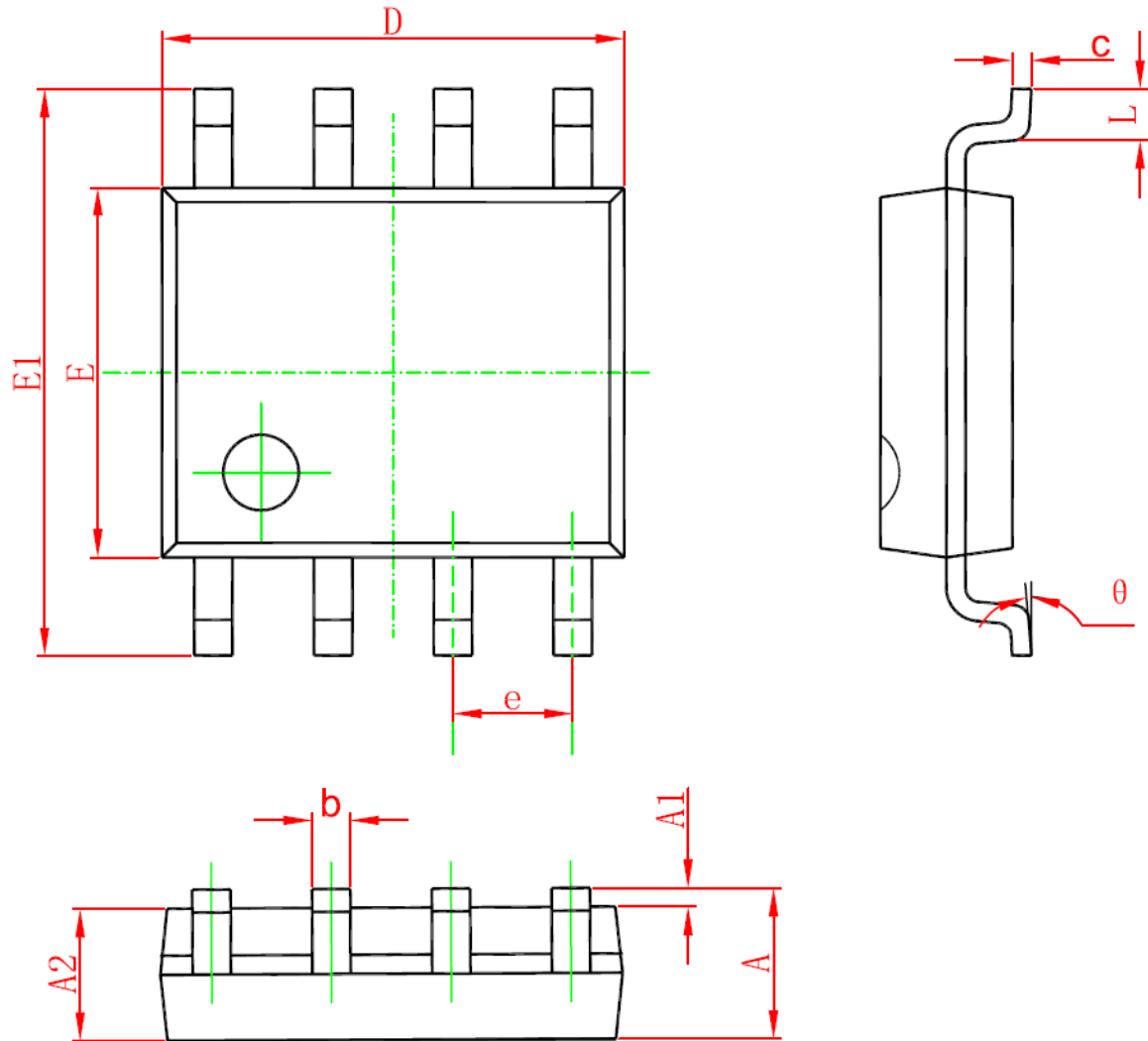


Ordering and Marking Information

| Ordering Device No. | Marking | Package | Packing | Quantity |
|---------------------|---------|---------|-----------|-----------|
| ASDM20P13S-R | 20P13 | SOP8 | Tape&Reel | 4000/Reel |

| PACKAGE | MARKING |
|---------|--|
| SOP-8 |  <p>AS □□ → Lot Number 20P13 □□□□ → Date Code</p> |

SOP-8 PACKAGE IN FORMATION



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



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